

IN THE CLAIMS

The status of the claims as presently amended is as follows:

1. *(Previously Presented)* A MIS-type semiconductor device comprising:
 - a source region of a first conductivity type;
 - a base region of a second conductivity type;
 - a drift region of the first conductivity type;
 - a gate insulation film on the base region;
 - a gate electrode formed on the gate insulation film;
 - a source electrode connected electrically to the source region;
 - an interlayer insulation film insulating the gate electrode and the source electrode from each other;
 - an insulation film on the drift region and adjacent to the gate electrode; and
 - a field plate on the insulation film, the field plate being connected to the source electrode,wherein the insulation film is thinner than the interlayer insulation film.
2. *(Canceled)*
3. *(Original)* The MIS-type semiconductor device according to claim 1, wherein the insulation film is as thin as or thicker than the gate insulation film and as thick as or thinner than V_b/E_c , where V_b is the breakdown voltage of the MIS-type semiconductor device and E_c is the critical dielectric breakdown strength of silicon.
4. *(Previously Presented)* The MIS-type semiconductor device according to claim 1, wherein the drift region comprises a first drift region and a second drift region, the first drift region being doped heavier than the second drift region, at least a part of the surfaces of the first drift region and the gate electrode overlap each other, and an edge of the second drift region is positioned farther from the gate electrode than the first drift region so that the second drift region is not exposed to the surface of the base region beneath the gate electrode.
- 5-6. *(Canceled)*
7. *(Original)* The MIS-type semiconductor device according to claim 4, wherein the second drift region is larger in volume than the first drift region.

8-9. (*Canceled*)

10. (*Original*) The MIS-type semiconductor device according to claim 4, wherein the diffusion depth of the second drift region is longer than the diffusion depth of the first drift region.

11-15. (*Canceled*)

16. (*Original*) The MIS-type semiconductor device according to claim 4, wherein the net impurity amount per a unit length in the second drift region is larger than the net impurity amount per a unit length in the first drift region.

17-27. (*Canceled*)

28. (*Original*) The MIS-type semiconductor device according to claim 4, further including a drain region spaced from the first drift region.

29-137. (*Canceled*)

138. (*Withdrawn*) A MIS-type semiconductor device according to claim 4, further including a semiconductor chip having a first major surface and a second major surface facing opposite to each other, and a drain region of the first conductivity type connected to the drift region, wherein the source region, the base region, and the drift region are on the side of the first major surface, and the drift region is spaced from the source region.

139. (*Withdrawn*) A MIS-type semiconductor device according to claim 4, further including a semiconductor chip having a first major surface and a second major surface facing opposite to each other, and a drain region of the first conductivity type on the side of the second major surface, the drain region being connected to the drift region, wherein the source region, the base region, and the drift region are on the side of the first major surface, and the drift region is spaced apart from the source region.

140-200. (*Canceled*)